

## N- and P-Channel 20-V (D-S) MOSFET

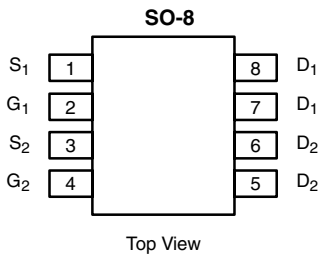
| PRODUCT SUMMARY |              |                             |           |
|-----------------|--------------|-----------------------------|-----------|
|                 | $V_{DS}$ (V) | $r_{DS(on)}$ ( $\Omega$ )   | $I_D$ (A) |
| N-Channel       | 20           | 0.0145 at $V_{GS} = 10$ V   | 9.6       |
|                 |              | 0.017 at $V_{GS} = 4.5$ V   | 8.6       |
| P-Channel       | - 20         | 0.033 at $V_{GS} = - 4.5$ V | - 6.2     |
|                 |              | 0.050 at $V_{GS} = - 2.5$ V | - 5       |

### FEATURES

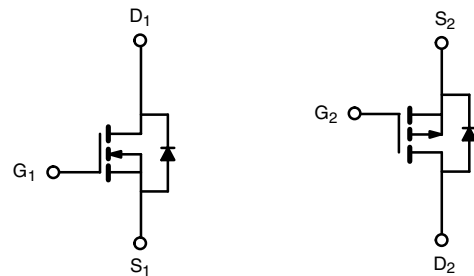
- TrenchFET<sup>®</sup> Power MOSFET

### APPLICATIONS

- Level Shift
- Load Switch



Ordering Information: Si4511DY-T1  
Si4511DY-T1-E3 (Lead (Pb)-Free)



| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted |                |               |        |           |        |       |   |
|--|----------------|---------------|--------|-----------|--------|-------|---|
| Parameter  | Symbol         | N-Channel     |        | P-Channel |        | Unit  |   |
|  |                | 10 secs       | Steady | 10 secs   | Steady |       |   |
| Drain-Source Voltage   | $V_{DS}$       | 20            |        | - 20      |        | V     |   |
| Gate-Source Voltage  | $V_{GS}$       | $\pm 16$      |        | $\pm 12$  |        |       |   |
| Continuous Drain Current ( $T_J = 150$ °C) <sup>a, b</sup>     | $I_D$          | $T_A = 25$ °C | 9.6    | 7.2       | - 6.2  | - 4.6 | A |
|  |                | $T_A = 70$ °C | 7.7    | 5.8       | - 4.9  | - 3.7 |   |
| Pulsed Drain Current   | $I_{DM}$       | 40            |        | - 40      |        | A     |   |
| Continuous Source Current (Diode Conduction) <sup>a</sup>      | $I_S$          | 1.7           | 0.9    | - 1.7     | 0.9    |       |   |
| Maximum Power Dissipation <sup>a</sup>                         | $P_D$          | $T_A = 25$ °C | 2      | 1.1       | 2      | 1.1   | W |
|  |                | $T_A = 70$ °C | 1.3    | 0.7       | 1.3    | 0.7   |   |
| Operating Junction and Storage Temperature Range               | $T_J, T_{stg}$ | - 55 to 150   |        |           |        | °C    |   |

| THERMAL RESISTANCE RATINGS               |            |                 |     |           |     |      |      |
|--|------------|-----------------|-----|-----------|-----|------|------|
| Parameter                                | Symbol     | N-Channel       |     | P-Channel |     | Unit |      |
|  |            | Typ             | Max | Typ       | Max |      |      |
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | $t \leq 10$ sec | 50  | 62.5      | 50  | 62.5 | °C/W |
|  |            | Steady State    | 85  | 110       | 90  | 110  |      |
| Maximum Junction-to-Foot (Drain)         | $R_{thJF}$ | 30              | 40  | 30        | 35  |      |      |

**Notes**

- a. Surface Mounted on 1" x 1" FR4 Board.  
b.  $t \leq 10$  sec

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |              |  |      |      |        |           |               |
|---|--------------|--|------|------|--------|-----------|---------------|
| Parameter   | Symbol       | Test Condition   | Min  | Typ  | Max    | Unit      |               |
| <b>Static</b>   |              |  |      |      |        |           |               |
| Gate Threshold Voltage  | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$  | N-Ch | 0.6  |        | 1.8       | V             |
|   |              | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$   | P-Ch | -0.6 |        | 1.4       |               |
| Gate-Body Leakage   | $I_{GSS}$    | $V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$  | N-Ch |      |        | $\pm 100$ | nA            |
|   |              | $V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$  | P-Ch |      |        | $\pm 100$ |               |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$  | N-Ch |      |        | 1         | $\mu\text{A}$ |
|   |              | $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$   | P-Ch |      |        | -1        |               |
|   |              | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$  | N-Ch |      |        | 5         |               |
|   |              | $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$   | P-Ch |      |        | -5        |               |
| On-State Drain Current <sup>b</sup>   | $I_{D(on)}$  | $V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$  | N-Ch | 40   |        |           | A             |
|   |              | $V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$   | P-Ch | -40  |        |           |               |
| Drain-Source On-State Resistance <sup>b</sup>                                   | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 9.6\text{ A}$   | N-Ch |      | 0.0115 | 0.0145    | $\Omega$      |
|   |              | $V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$  | P-Ch |      | 0.022  | 0.033     |               |
|   |              | $V_{GS} = 4.5\text{ V}, I_D = 8.6\text{ A}$  | N-Ch |      | 0.0135 | 0.017     |               |
|   |              | $V_{GS} = -2.5\text{ V}, I_D = -5\text{ A}$  | P-Ch |      | 0.035  | 0.050     |               |
| Forward Transconductance <sup>b</sup>   | $g_{fs}$     | $V_{DS} = 15\text{ V}, I_D = 9.6\text{ A}$   | N-Ch |      | 33     |           | S             |
|   |              | $V_{DS} = -15\text{ V}, I_D = -6.2\text{ A}$   | P-Ch |      | 17     |           |               |
| Diode Forward Voltage <sup>b</sup>  | $V_{SD}$     | $I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$  | N-Ch |      | 0.8    | 1.2       | V             |
|   |              | $I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$   | P-Ch |      | -0.8   | -1.2      |               |
| <b>Dynamic<sup>a</sup></b>  |              |  |      |      |        |           |               |
| Total Gate Charge   | $Q_g$        | N-Channel<br>$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 9.6\text{ A}$<br>P-Channel<br>$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$  | N-Ch |      | 11.5   | 18        | nC            |
| Gate-Source Charge  | $Q_{gs}$     |  | N-Ch |      | 3.7    |           |               |
| Gate-Drain Charge   | $Q_{gd}$     |  | P-Ch |      | 4.1    |           |               |
| Turn-On Delay Time  | $t_{d(on)}$  | N-Channel<br>$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$<br>$I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$<br>P-Channel<br>$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$<br>$I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$ | N-Ch |      | 12     | 20        | ns            |
| Rise Time   | $t_r$        |  | N-Ch |      | 12     | 20        |               |
| Turn-Off Delay Time   | $t_{d(off)}$ |  | N-Ch |      | 55     | 85        |               |
| Fall Time   | $t_f$        |  | P-Ch |      | 70     | 105       |               |
| Source-Drain Reverse Recovery Time  | $t_{rr}$     | $I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$   | N-Ch |      | 50     | 100       |               |
|   |              | $I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$  | P-Ch |      | 40     | 80        |               |

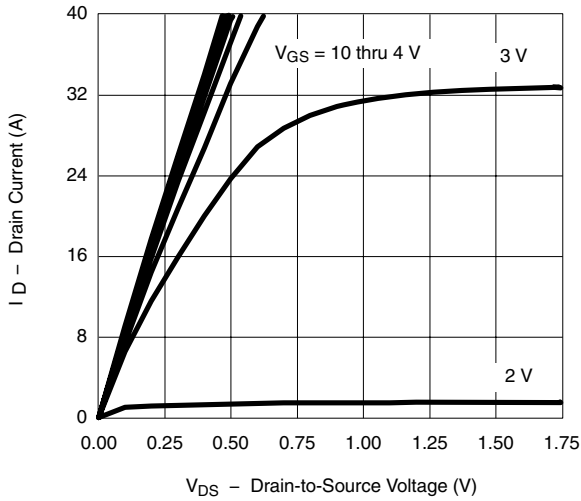
## Notes

- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

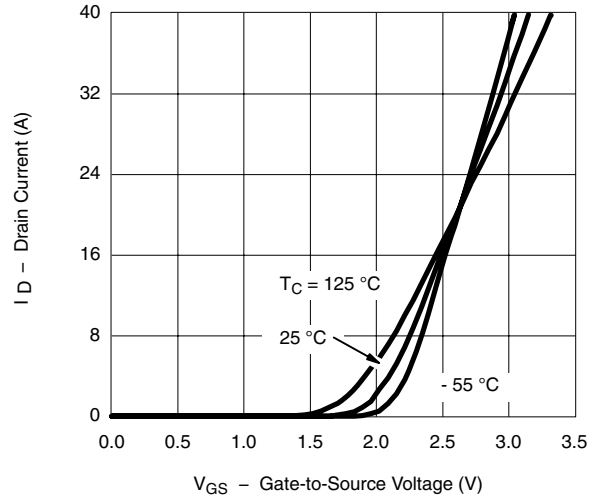
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



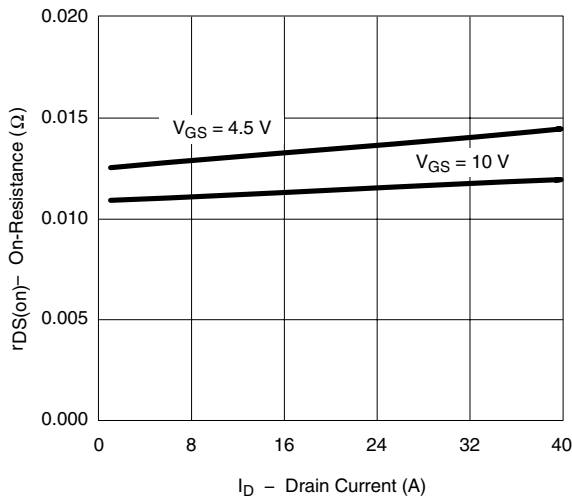
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless noted



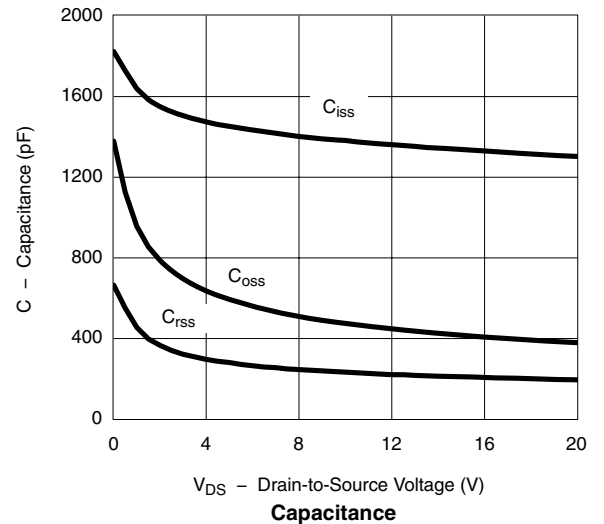
**Output Characteristics**



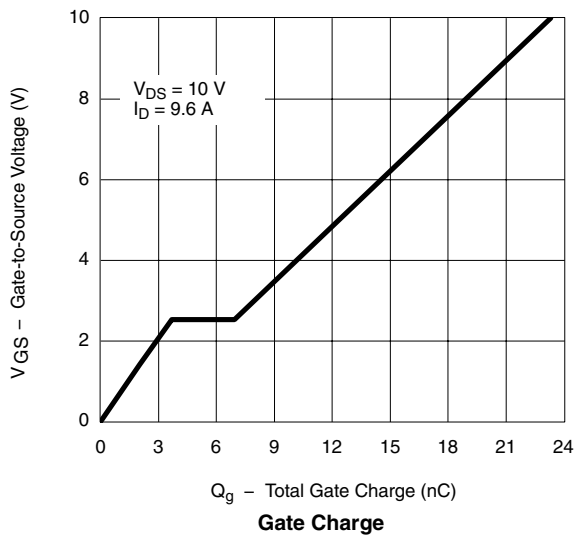
**Transfer Characteristics**



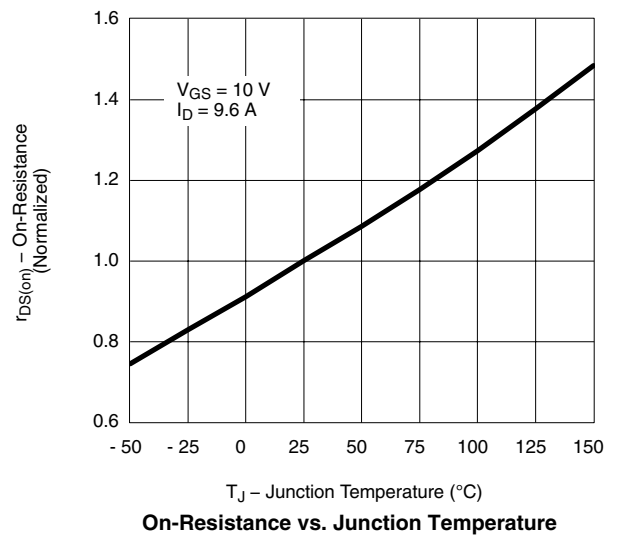
**On-Resistance vs. Drain Current**



**Capacitance**

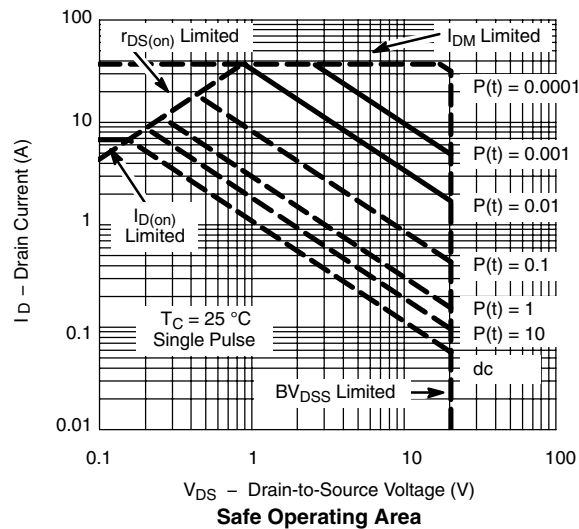
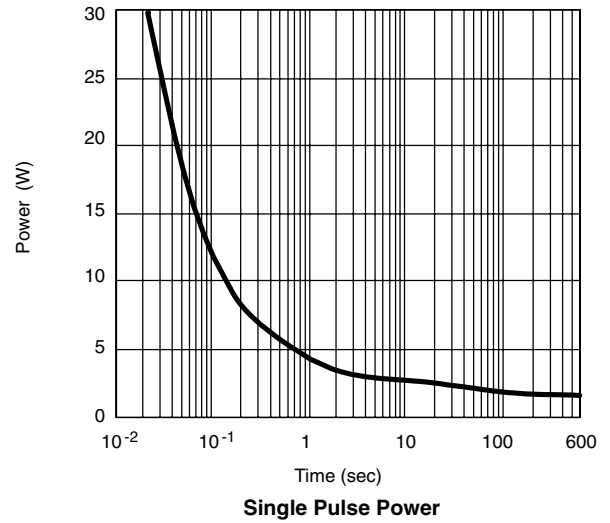
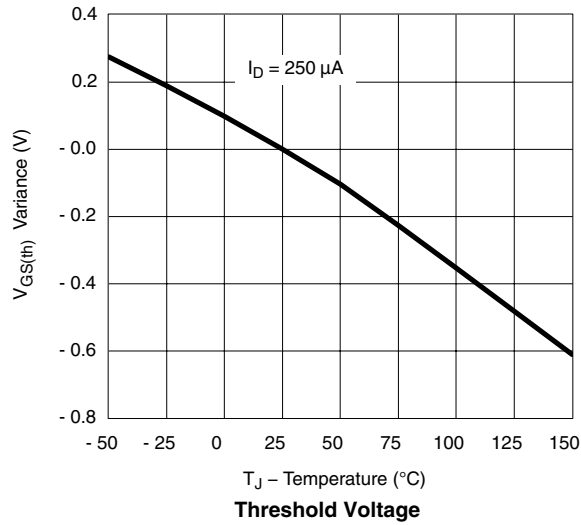
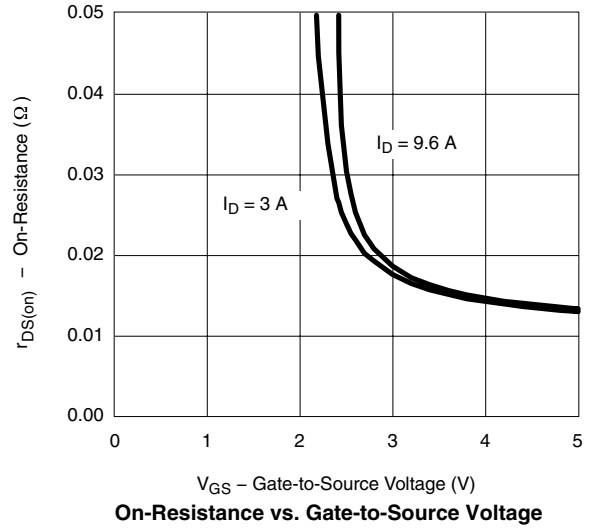
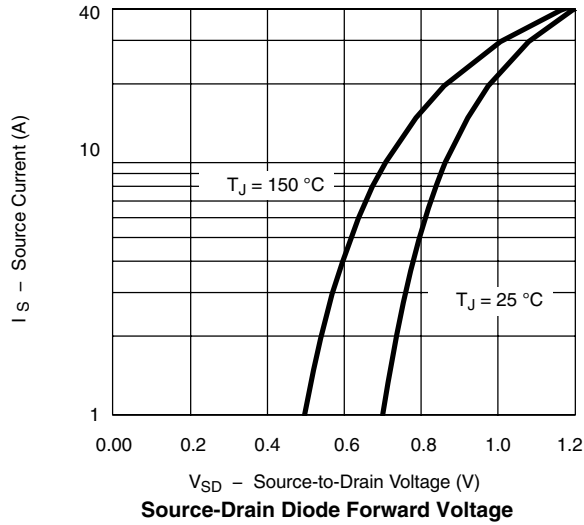


**Gate Charge**



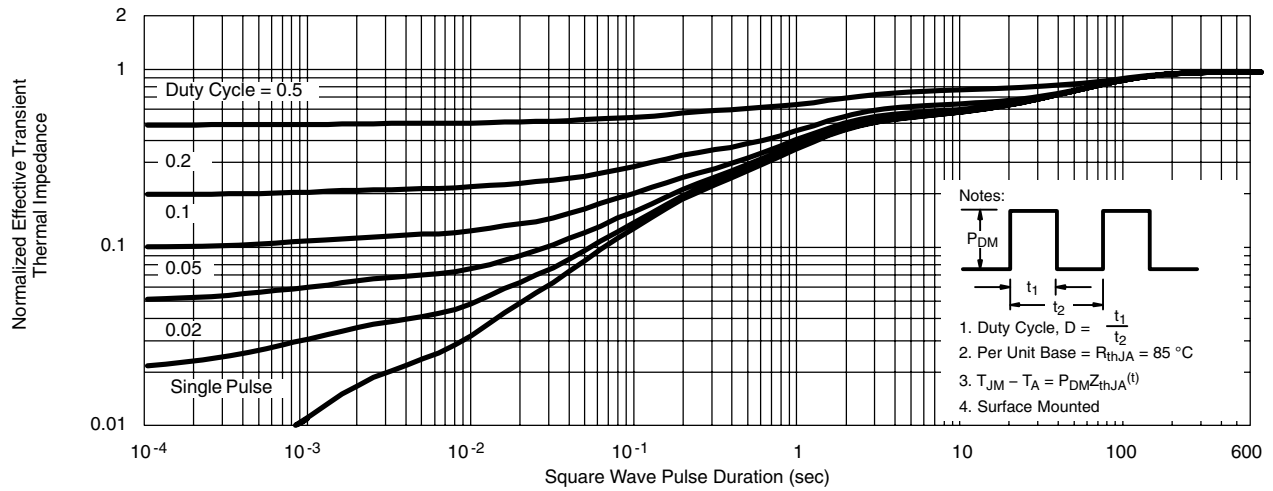
**On-Resistance vs. Junction Temperature**

## N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

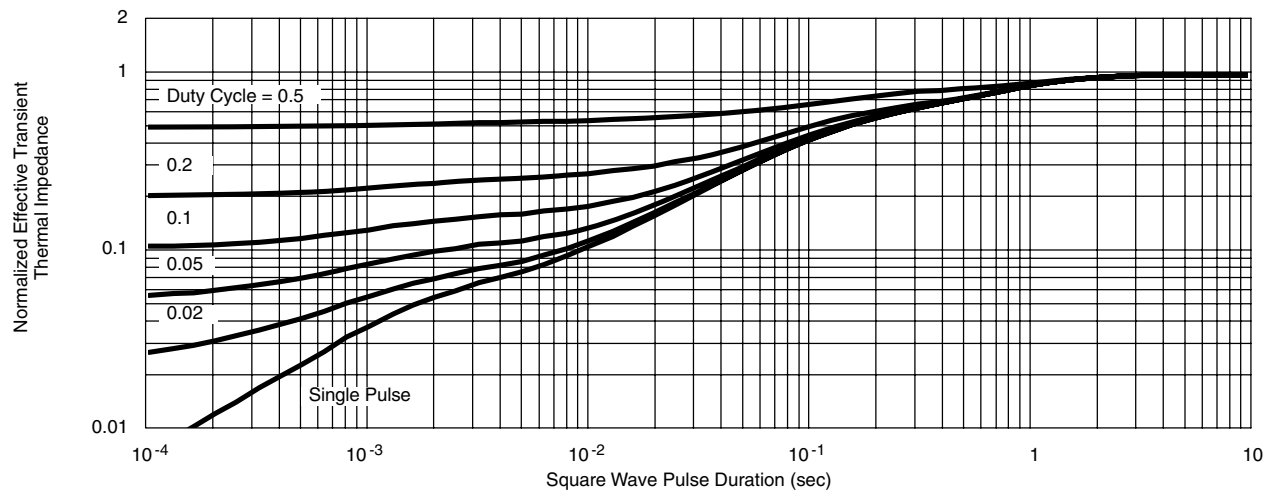




**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless noted

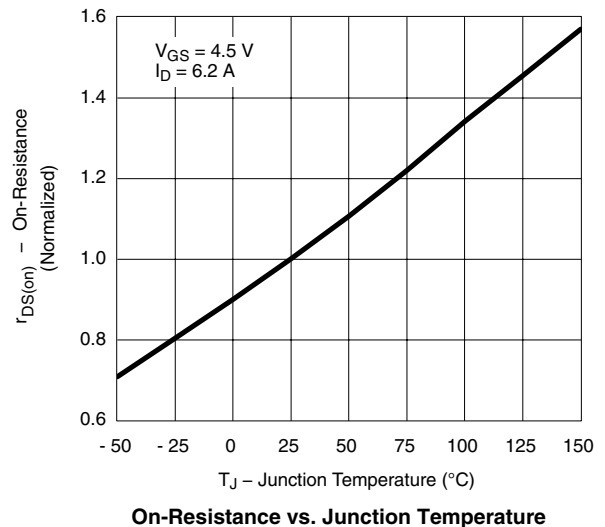
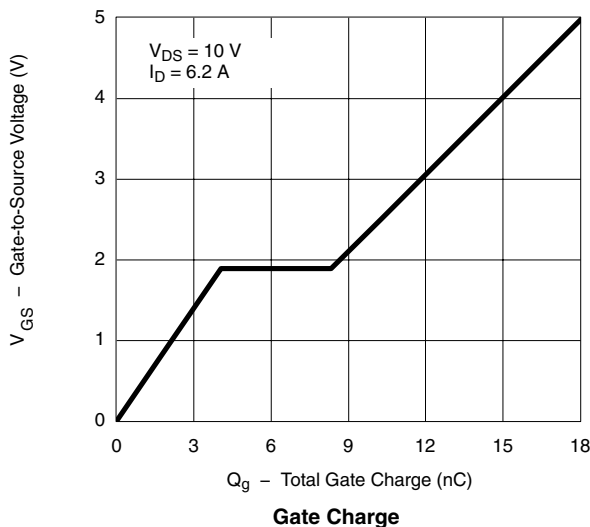
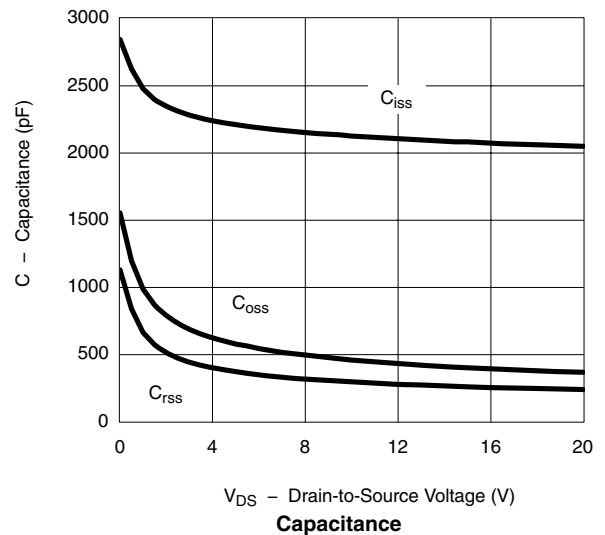
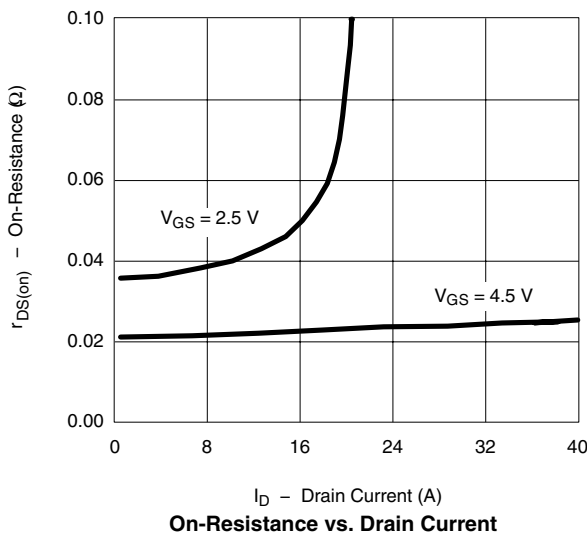
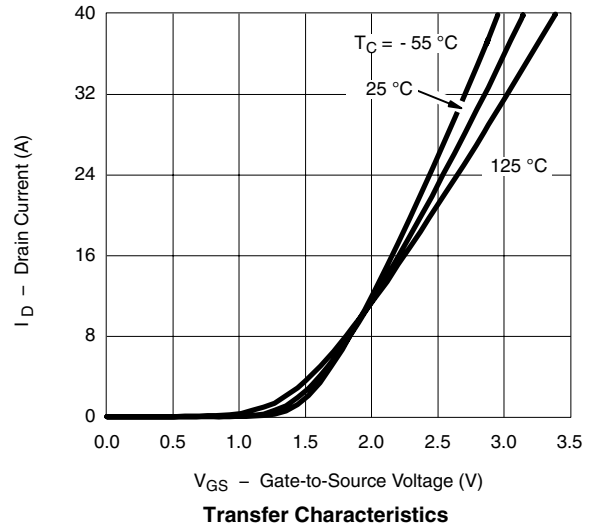
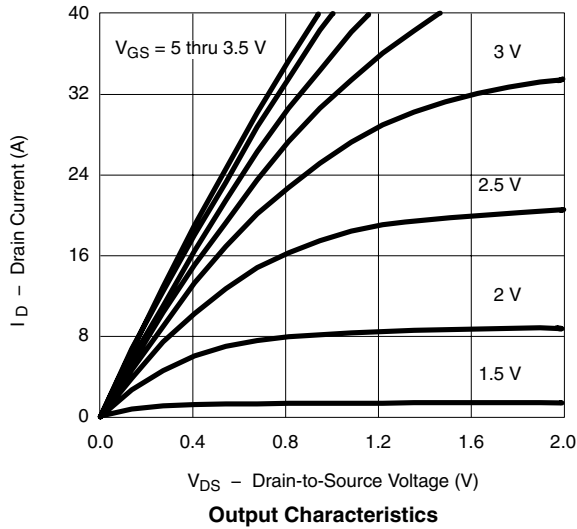


**Normalized Thermal Transient Impedance, Junction-to-Ambient**



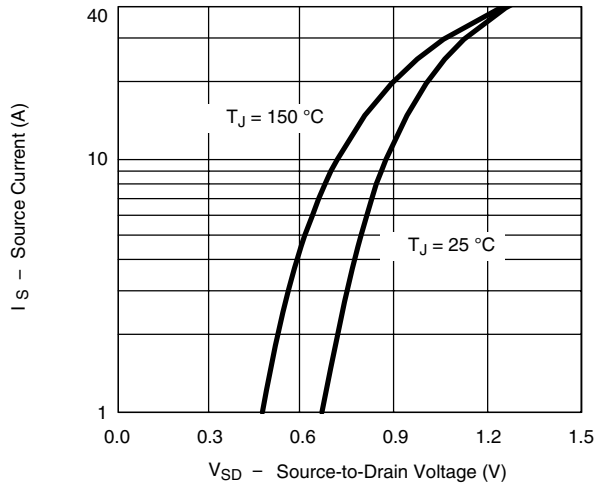
**Normalized Thermal Transient Impedance, Junction-to-Foot**

## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

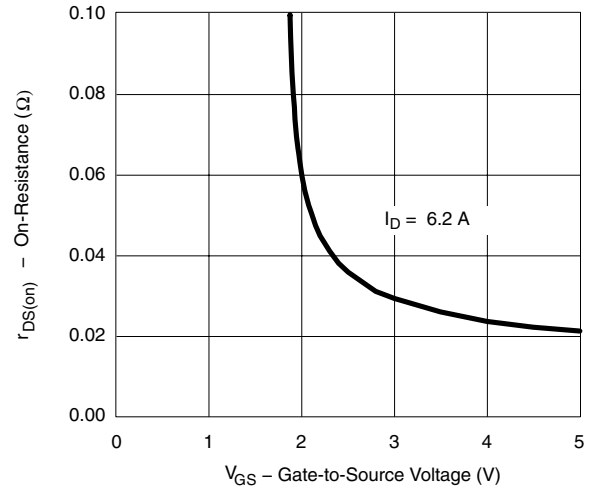




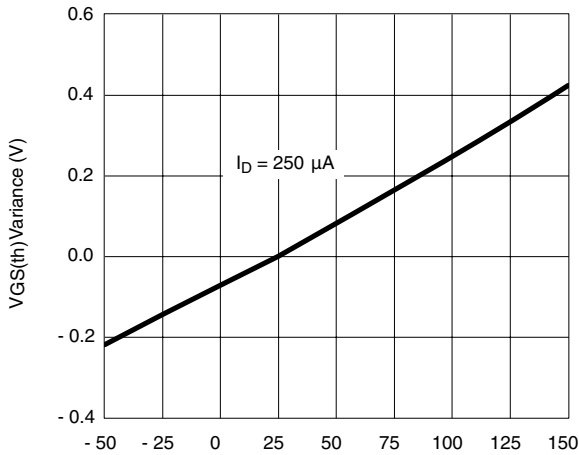
**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless noted



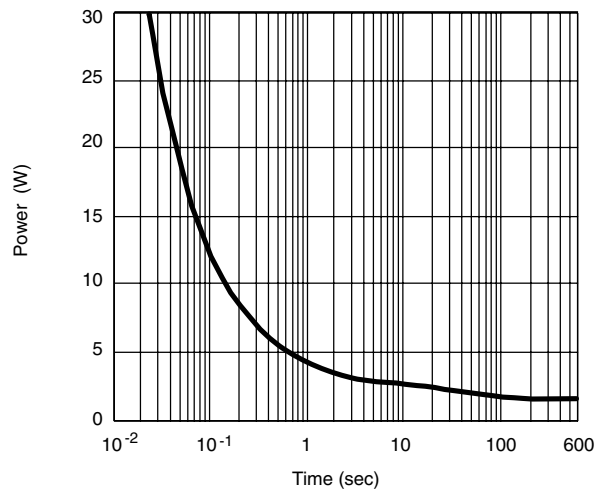
**Source-Drain Diode Forward Voltage**



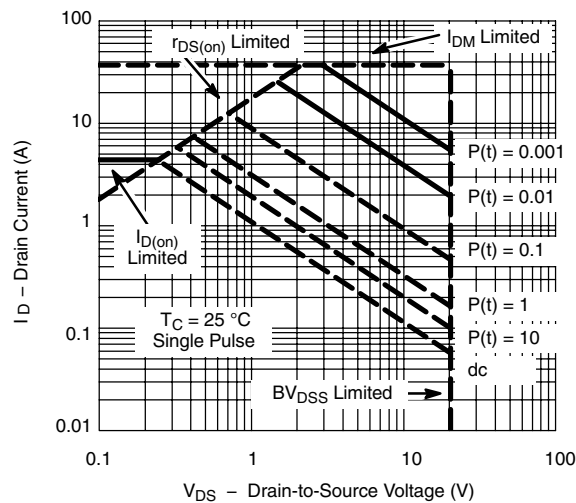
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**

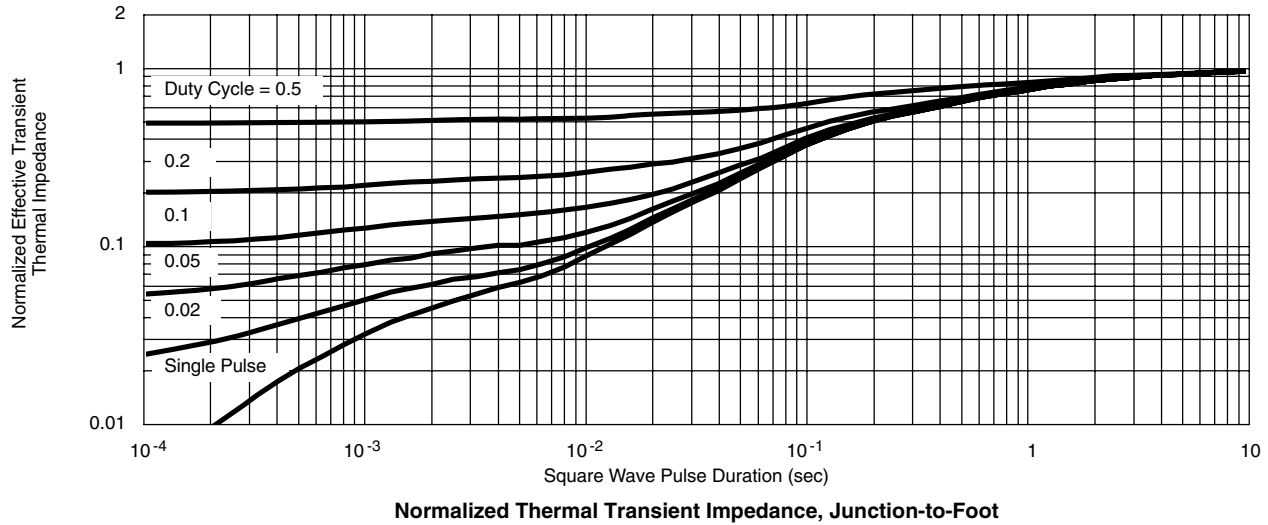
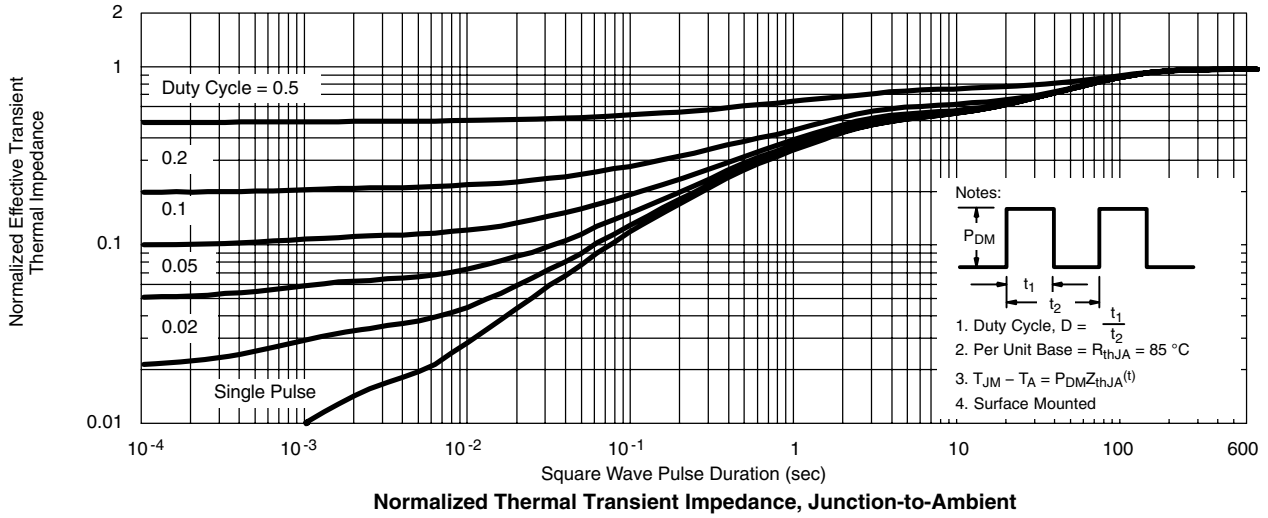


**Single Pulse Power**



**Safe Operating Area**

**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless noted



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